

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

Features

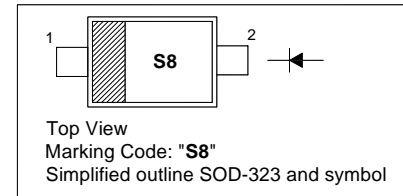
- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

Applications

- High speed switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM}	40	V
Reverse Voltage	V _R	30	V
Mean Rectifying Current	I _O	30	mA
Peak Forward Surge Current (60 Hz for 1 Cyc.)	I _{FSM}	200	mA
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _s	- 40 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I _F = 1 mA	V _F	-	0.37	V
Reverse Current at V _R = 30 V	I _R	-	0.5	μA
Capacitance Between Terminals at V _R = 1 V, f = 1 MHz	C _T	2	-	pF

Note: ESD sensitive product handling required.

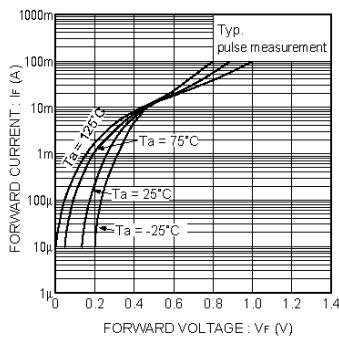


Fig. 1 Forward characteristics

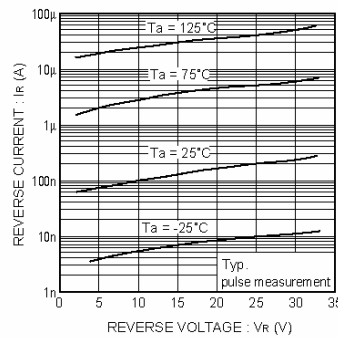


Fig. 2 Reverse characteristics

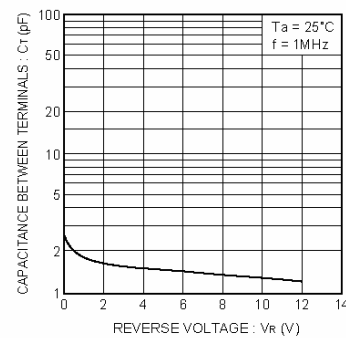
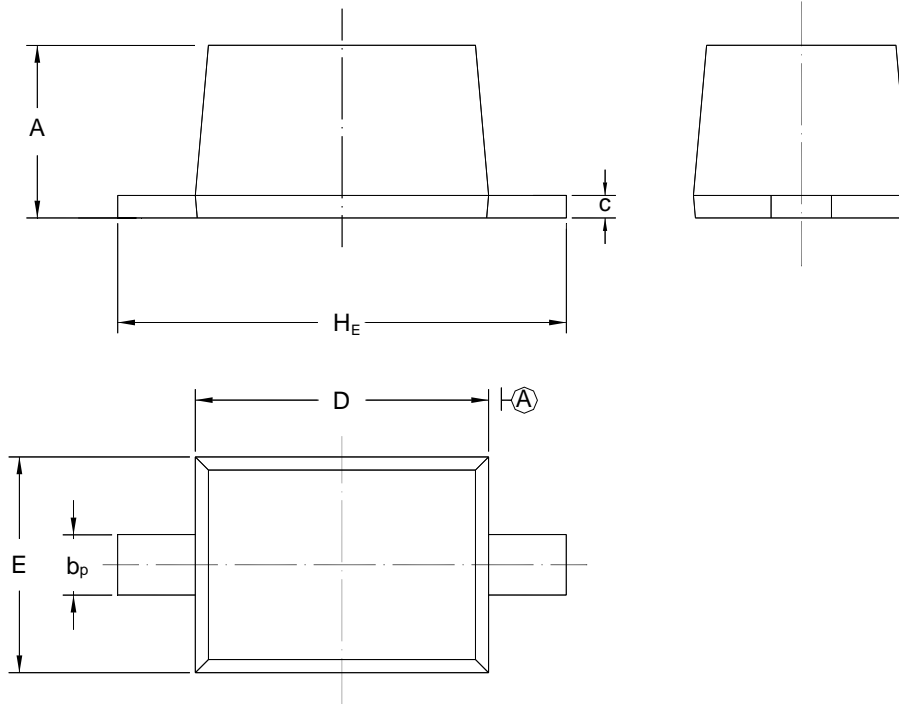


Fig. 3 Capacitance between terminals characteristics

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b _p	C	D	E	H _E
mm	1.10 0.80	0.40 0.25	0.15 0.00	1.80 1.60	1.35 1.15	2.80 2.30